



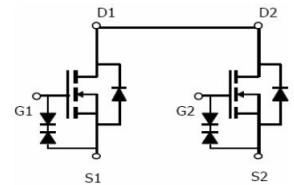
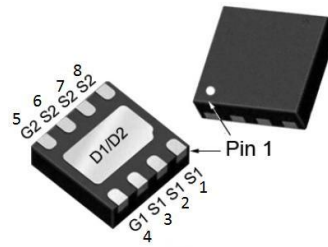
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

BVDSS	R _{DS(on)}	ID
20V	3.2mΩ	50A

DFN3030-8L Pin Configurations
FEATURE

- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$
- Low Gate Charge
- High Power and Current Handling Capability
- Surface Mount Package
- ESD Rating:2000V HBM


ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	50	A
Pulsed Drain Current (note 1)	I_{DM}	100	A
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	38	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS
T_a =25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERICTISCS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =19V, V _{GS} = 0V			1	uA
Gate-body leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} = 0V			±7	uA
Gate threshold voltage (note 3)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	0.6	1.0	V
Drain-source on-resistance (note 3)	R _{DS(on)}	V _{GS} =4.5V, I _D =8.0A		3.2	3.7	mΩ
		V _{GS} =2.5V, I _D =6.0A		4.2	4.8	mΩ
Forward tranconductance (note 3)	g _{FS}	V _{DS} =5V, I _D =4A		10		S
Diode forward voltage (note 3)	V _{SD}	I _S =1.50A, V _{GS} = 0V			1.0	V
DYNAMIC CHARACTERICTISCS (note4)						
Input Capacitance	C _{iSS}	V _{DS} =10V, V _{GS} =0V, f =1MHz		2610		pF
Output Capacitance	C _{oss}			345		pF
Reverse Transfer Capacitance	C _{rSS}			322		pF
SWITCHING CHARACTERICTISCS (note 4)						
Turn-on delay time	t _{d(on)}	V _{GS} =4.5V, V _{DS} =10V, I _D =6A R _{GEN} =3Ω		8.2		ns
Turn-on rise time	t _r			35		ns
Turn-off delay time	t _{d(off)}			372		ns
Turn-off fall time	t _f			213		ns
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V, I _D =6A		36		nC
Gate-Source Charge	Q _{gs}			3.2		nC
Gate-Drain Charge	Q _{gd}			13.0		nC

Notes :

- 1.Repetitive rating: Pluse width limited by maximum junction temperature
- 2.Surface Mounted on FR4 board, t≤10 sec.
3. Pulse test : Pulse width≤300μs, duty cycle≤2%.
4. Guaranteed by design, not subject to production.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTIC

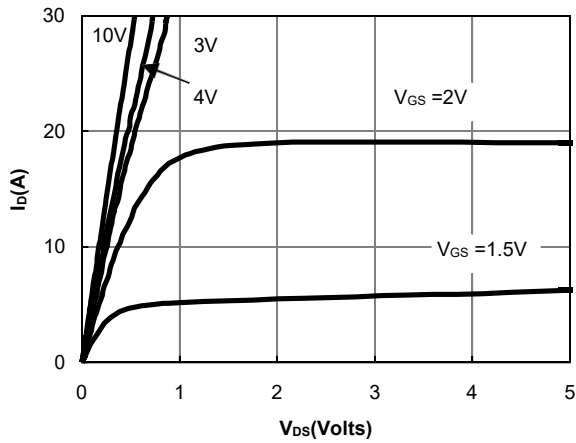


Figure 1: On-Regions Characteristic CS

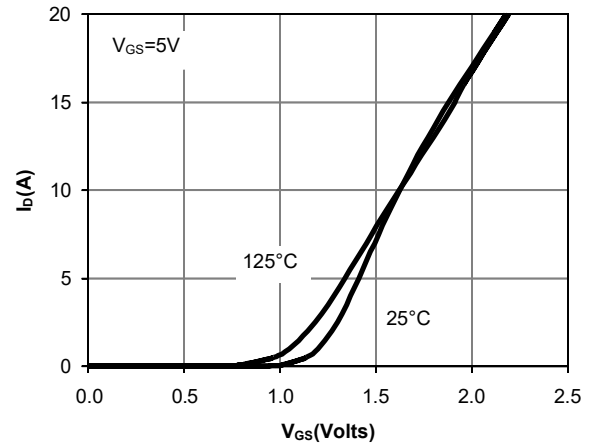


Figure 2: Transfer Characteristics

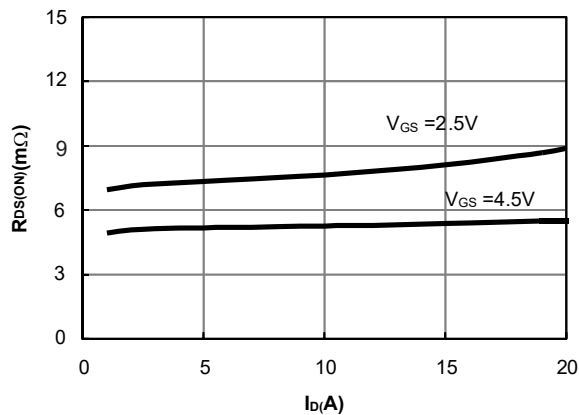


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

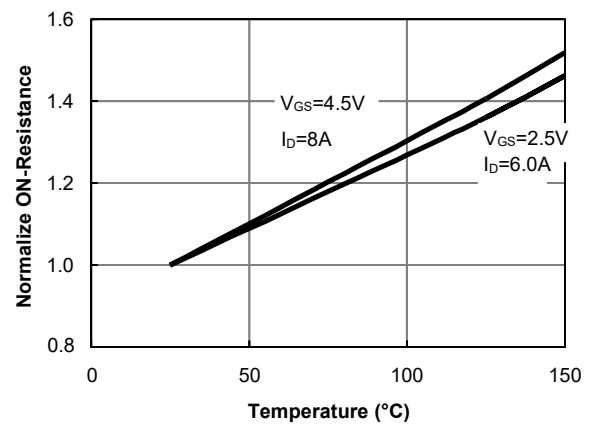


Figure 4: On-Resistance vs. Junction Temperature

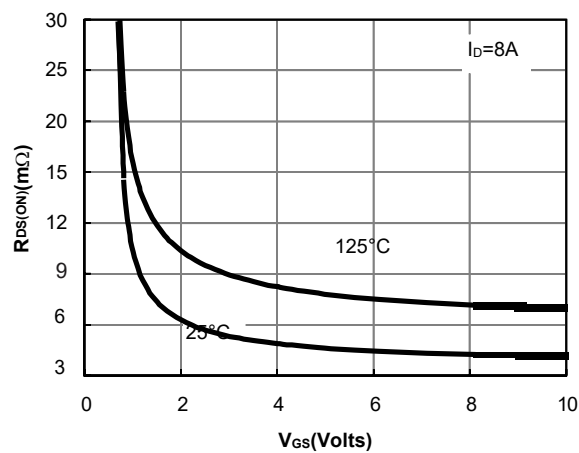


Figure 5: On-Resistance vs. Gate-Source Voltage

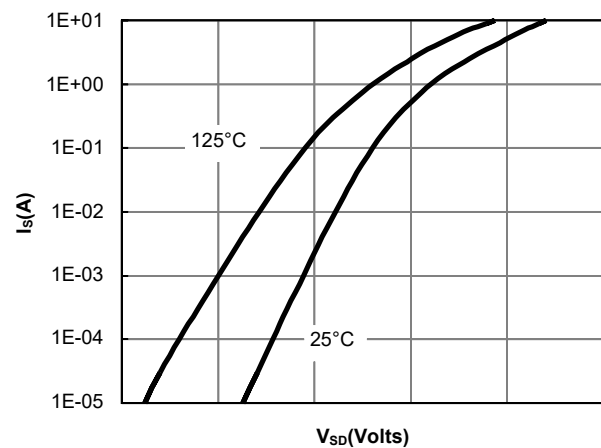


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTIC

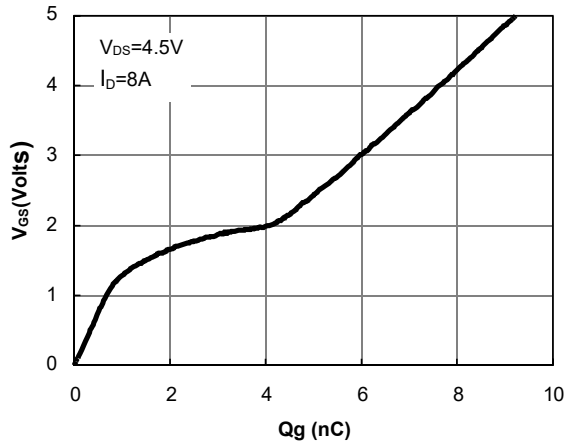


Figure 7: Gate-Charge Characteristics

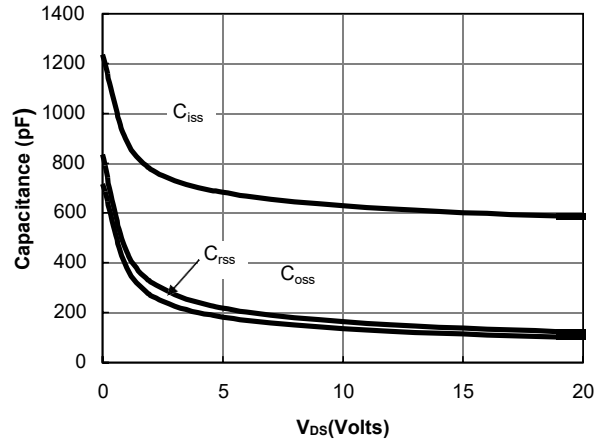


Figure 8: Capacitance Characteristics

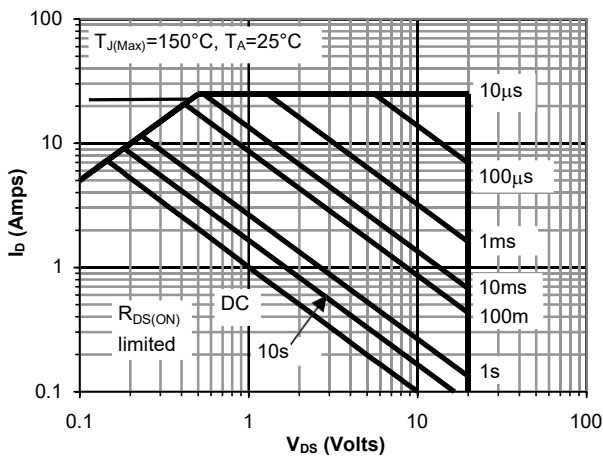


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

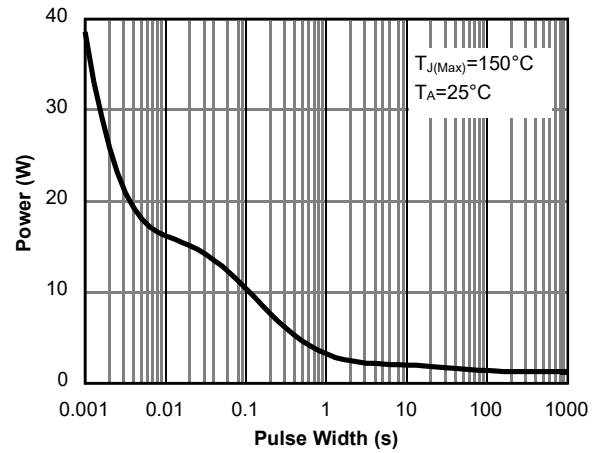


Figure 10: Single Pulse Power Rating Junction-to-Ambient

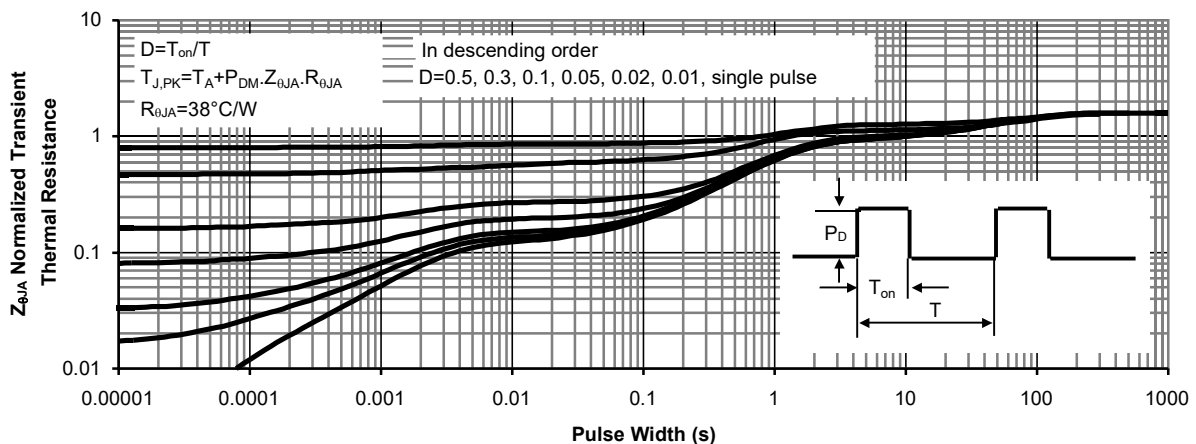
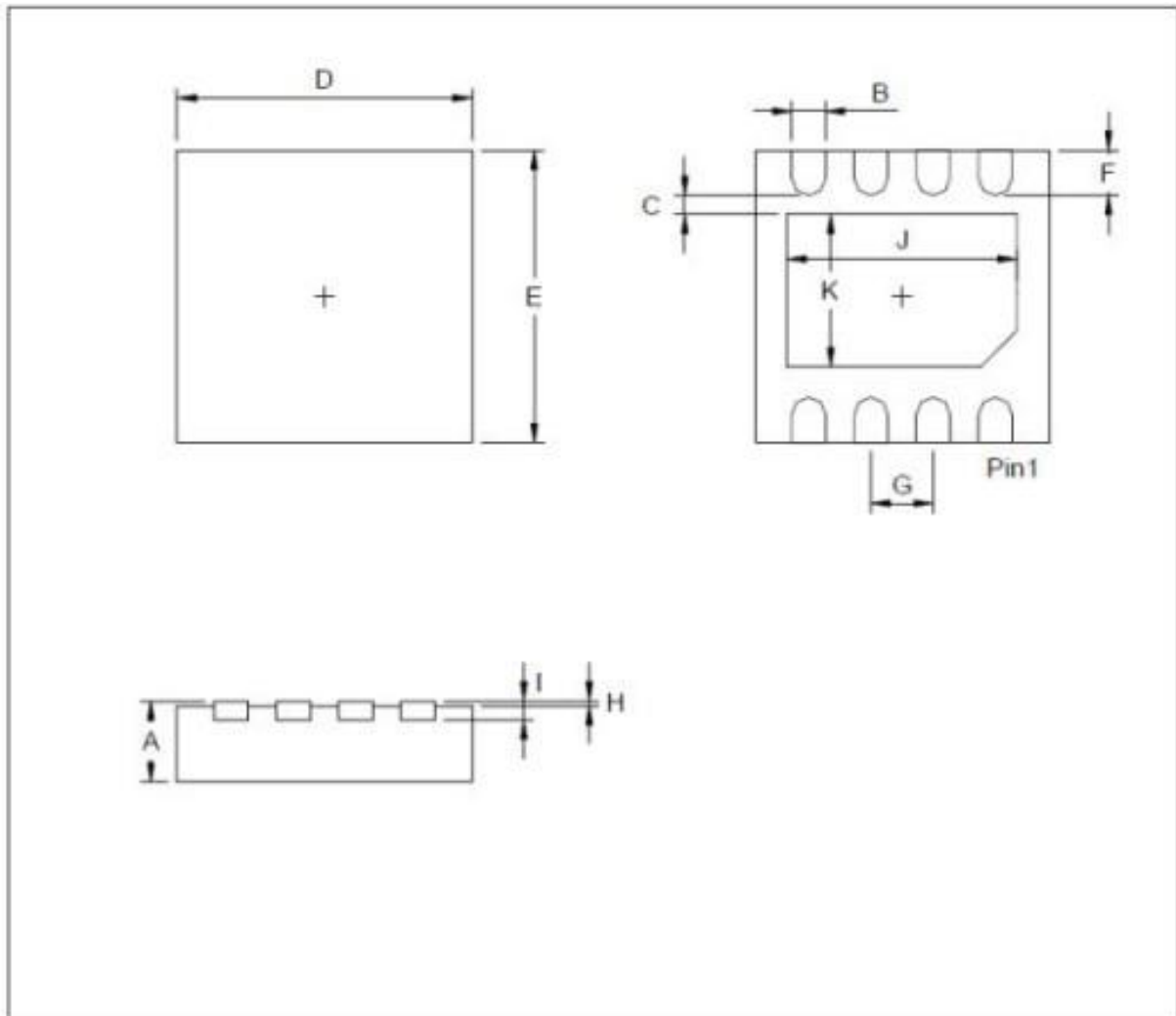


Figure 11: Normalized Maximum Transient Thermal Impedance

DFN3030-8L Package Outline Data



Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	0.7		0.8	I		0.203	
B	0.25		0.35	J	2.2		2.4
C	0.2			K	1.4		1.6
D	2.924		3.076				
E	2.924		3.076				
F	0.324		0.476				
G		0.65					
H	0		0.05				